

MAPR-001090-350S00

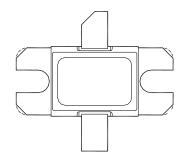
Rev. V2

Features

- NPN Silicon Microwave Power Transistors
- Common Base Configuration
- Broadband Class C Operation
- · High Efficiency Inter-Digitized Geometry
- · Diffused Emitter Ballasting Resistors
- · Gold Metallization System
- Internal Input & Output Impedance Matching
- Hermetic Metal/Ceramic Package
- RoHS* Compliant



- · Aerospace & Defense
- ISM



Electrical Specifications: Freq. = 1090 MHz, $T_c = 25 \pm 5$ °C (Room Ambient)

Parameter	Test Conditions	Min.	Max.	Units
Collector-Emitter Breakdown Voltage	I _C = 250 mA	65	_	V
Collector-Emitter Leakage Current	V _{CE} = 50 V	_	15	mA
Thermal Resistance	V _{CC} = 50 V, P _{OUT} = 350 W	_	0.16	°C/W
Input Power	V _{CC} = 50 V, P _{OUT} = 350 W	_	44	W
Power Gain	V _{CC} = 50 V, P _{OUT} = 350 W	9	_	dB
Collector Efficiency	V _{CC} = 50 V, P _{OUT} = 350 W	45	_	%
Input Return Loss	V _{CC} = 50 V, P _{OUT} = 350 W	_	-9	dB
Load Mismatch Tolerance	V _{CC} = 50 V, P _{OUT} = 350 W	_	10:1	_
Load Mismatch Stability	V _{CC} = 50 V, P _{OUT} = 350 W	_	1.5:1	_

Absolute Maximum Ratings @ +25°C

Parameter	Rating	
Collector-Emitter Voltage	65 V	
Emitter-Base Voltage	3 V	
Collector Current (Peak)	25 A	
Power Dissipation	1.1 kW	
Storage Temperature	-65°C to +200°C	
Junction Temperature	+200°C	



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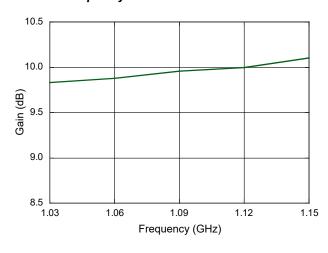
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Typical Broadband RF Performance

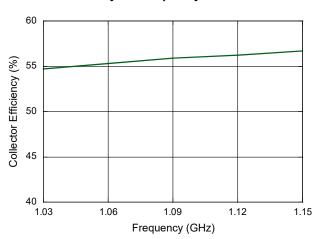
(Provided for information only - 100% Production testing performed at 1090 MHz only)

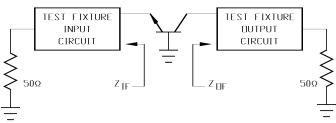
Freq. (MHz)	P _{IN} (W)	P _{OUT} (W)	Gain (dB)	I _C (A)	E _{FF} (%)	R _L (dB)	VSWR-S (1.5:1)	VSWR-T (10:1)
1025	37	350	9.81	12.8	54.6	-14.8	S	Р
1090	35	350	9.96	12.5	55.8	-16.7	S	Р
1150	34	350	10.10	12.4	56.6	-26.1	S	Р

Gain vs. Frequency



Collector Efficiency vs. Frequency





RF Test Fixture Impedance

F (MHz)	$Z_{IF}\left(\Omega\right)$	Z _{OF} (Ω)
960	1.8 - j3.7	2.2 - j2.8
1025	1.8 - j3.2	2.3 - j2.2
1090	1.8 - j2.7	2.4 - j1.7
1150	1.9 - j2.3	2.6 - j1.5
1215	2.0 - j1.9	2.8 - j1.3

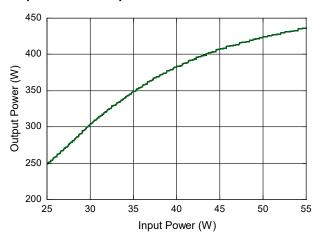


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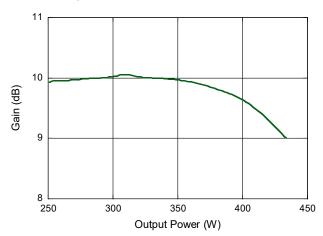
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RF Power Transfer Curves @ 1090 MHz

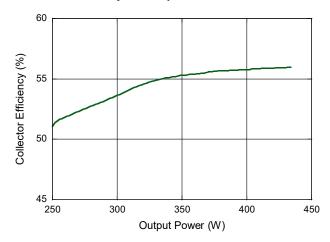
Output Power vs. Input Power



Gain vs. Output Power



Collector Efficiency vs. Output Power

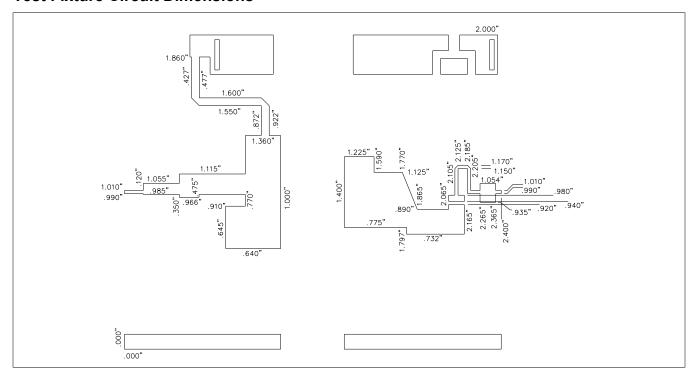




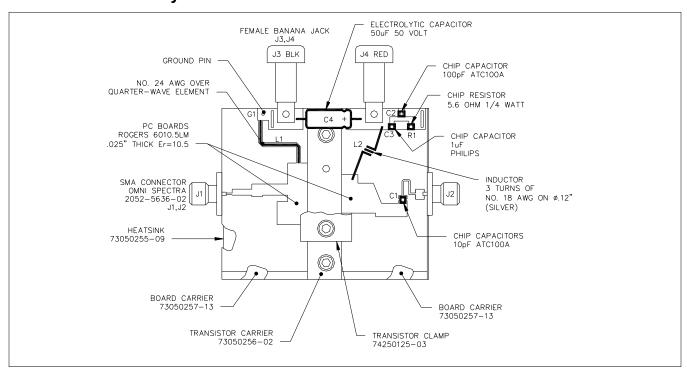
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Test Fixture Circuit Dimensions



Test Fixture Assembly

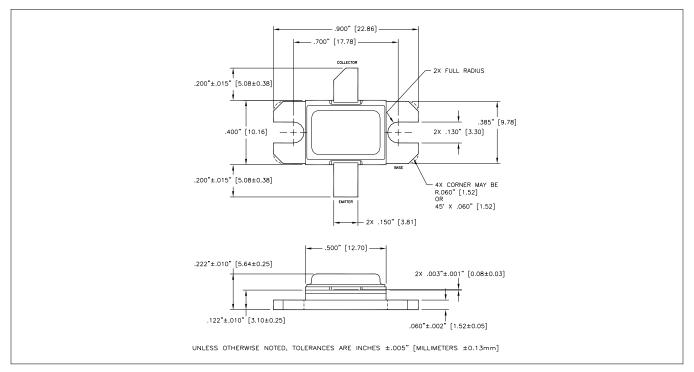




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Outline Drawing





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